



## N-Channel Reduced $Q_g$ , Fast Switching MOSFET

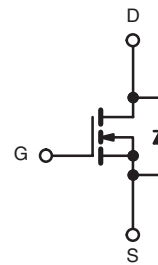
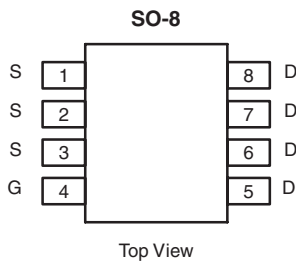
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.012 at $V_{GS} = 10$ V	$\pm 11$
	0.020 at $V_{GS} = 4.5$ V	$\pm 9$

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- High-Efficiency PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



N-Channel MOSFET

**Ordering Information:** Si4890DY-T1-E3 (Lead (Pb)-free)  
Si4890DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a, b</sup>	$I_D$	$T_A = 25$ °C	$\pm 11$
		$T_A = 70$ °C	$\pm 9$
Pulsed Drain Current (10 $\mu$ s Pulse Width)	$I_{DM}$	$\pm 50$	A
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	$I_S$	2.3	
Maximum Power Dissipation <sup>a, b</sup>	$P_D$	$T_A = 25$ °C	2.5
		$T_A = 70$ °C	1.6
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	$t \leq 10$ s	$R_{thJA}$		50	°C/W
	Steady State		70		

Notes:

a. Surface Mounted on FR4 board.

b.  $t \leq 10$  s.

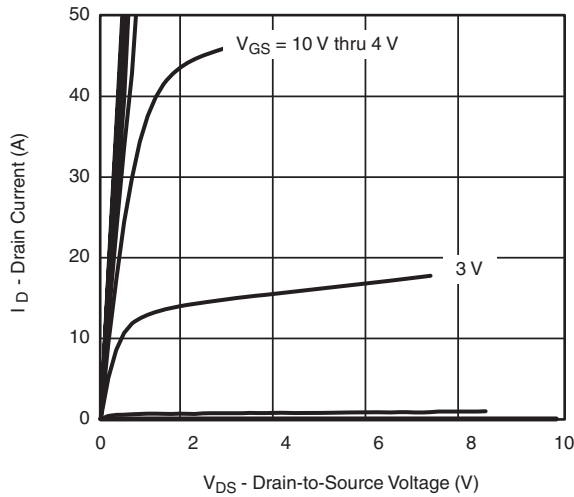
MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.8			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}$		0.0098	0.012	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$		0.0164	0.020	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 11\text{ A}$		21		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.3\text{ A}, V_{GS} = 0\text{ V}$		0.71	1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 5.0\text{ V}, I_D = 11\text{ A}$		14.2	20	nC
Gate-Source Charge	$Q_{gs}$			3.3		
Gate-Drain Charge	$Q_{gd}$			6.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		13	20	ns
Rise Time	$t_r$			8.5	15	
Turn-Off Delay Time	$t_{d(off)}$			35	53	
Fall Time	$t_f$			17	26	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = 2.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		35	

## Notes:

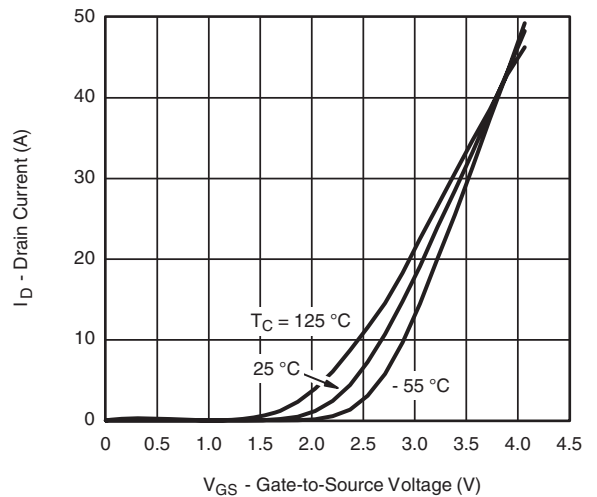
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

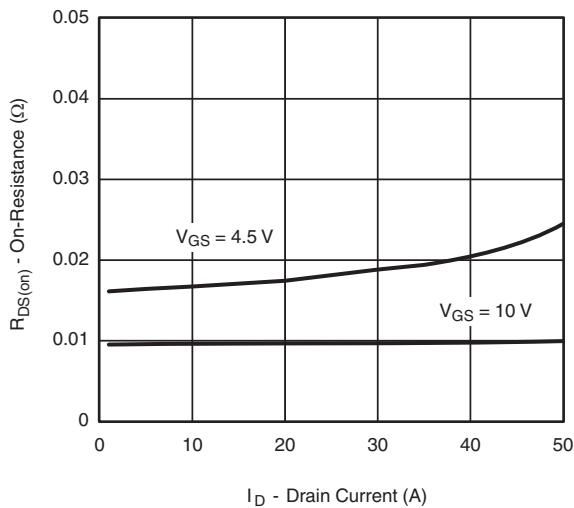
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



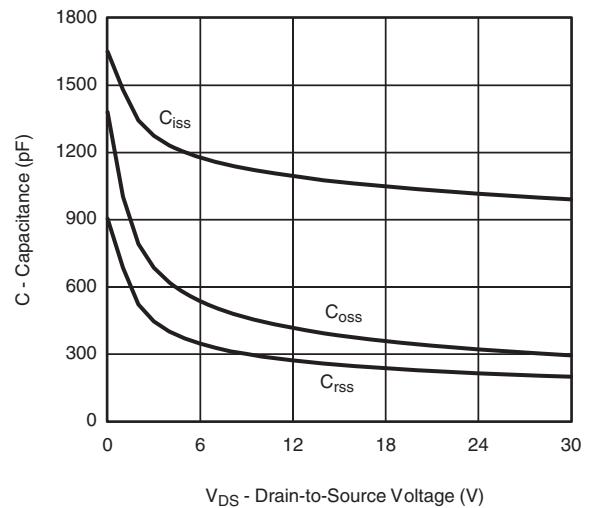
**Output Characteristics**



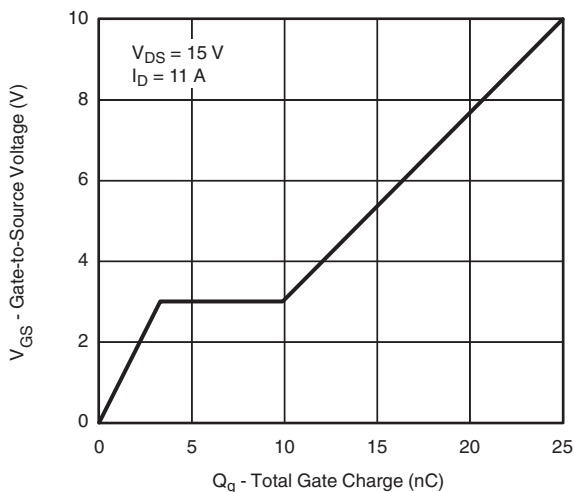
**Transfer Characteristics**



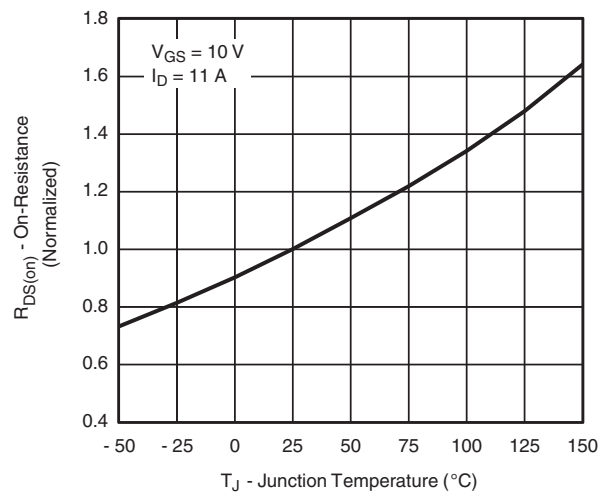
**On-Resistance vs. Drain Current**



**Capacitance**

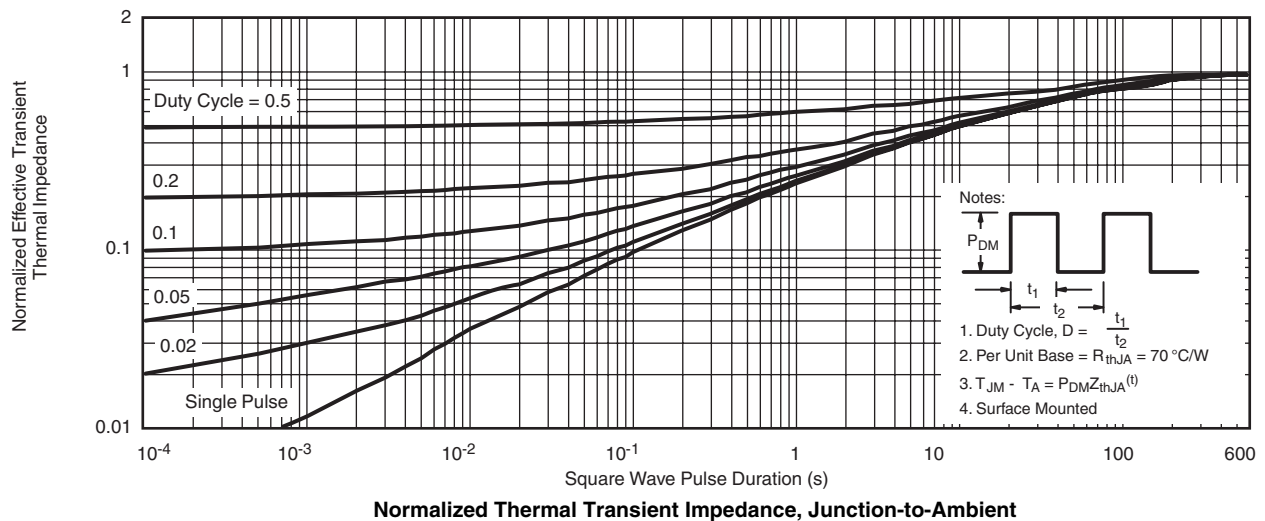
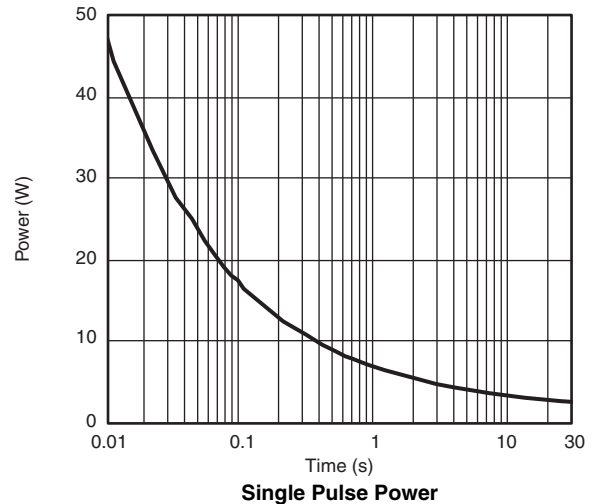
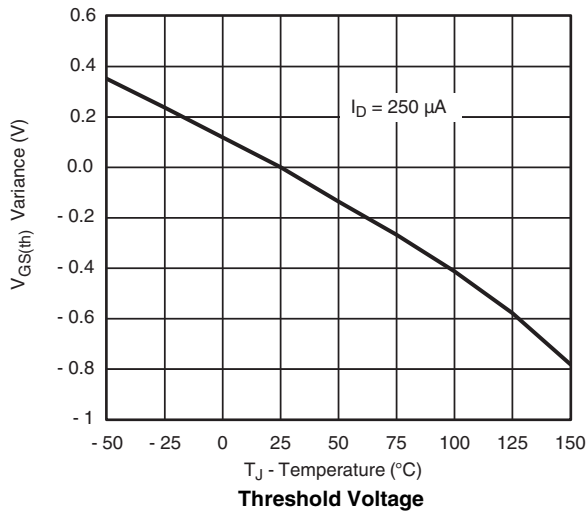
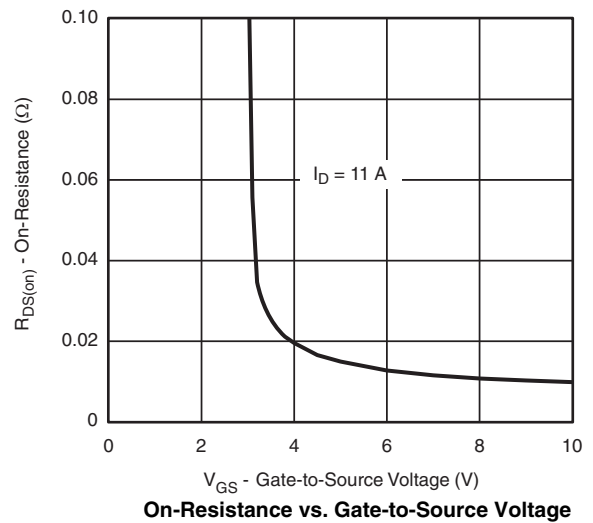
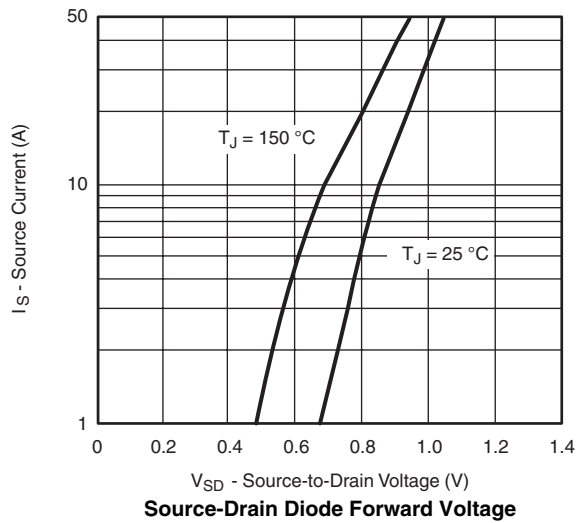


**Gate Charge**



**On-Resistance vs. Junction Temperature**

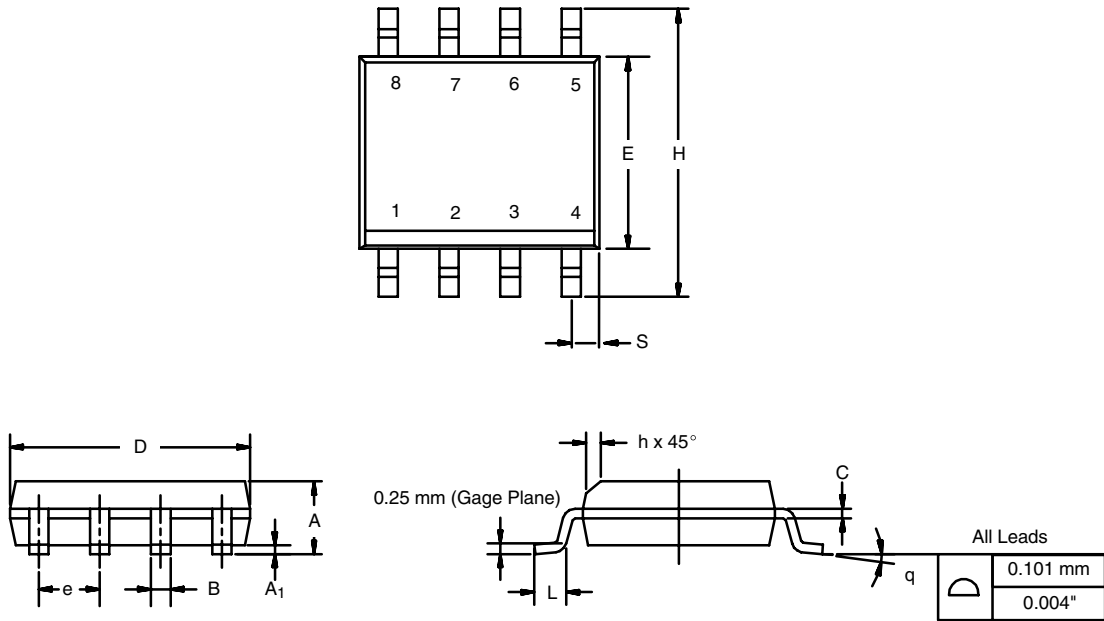
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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